

SRC0524P

Ultra Low Capacitance ESD Protection Array

Description

The ESD0524P provides a typical line to line capacitance of 0.5pF between I/O pins and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for HDMI applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

Features

- Protects two or four I/O lines
- Low capacitance: 0.5pF Typical between I/O channel
- Low leakage current
- 5V operating voltage
- Response time < 1ns
- Solid-state silicon avalanche technology
- Device meets MSL 1 requirements
- RoHS compliant

Applications

- High Definition Multi-Media Interface (HDMI)
- Digital Visual Interface (DVI)
- USB 1.1/2.0/3.0/OTG
- IEEE 1394 Firewire Ports
- Notebooks & Handhelds
- Projection TV & Monitors
- Set-top box
- Flat Panel Displays
- PCI Express

Mechanical Characteristics

- DFN2510 package
- Flammability Rating: UL 94V-0
- Terminal: Matte tin plated.
- Packaging: Tape and Reel
- High temperature soldering guaranted:260°C/10s
- Reel size: 7 inch



1	2	3	4	5
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10	9	8	7	6

Maximum Ratings And Characteristics @ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Units	
P _{PP}	Peak Pulse Power (8/20µs)	150	W	
I _{PP}	Peak Pulse Current (8/20µs)	5	А	
V _{ESD}	ESD per IEC 61000-4-2 (Air)	±15	kV	
	ESD per IEC 61000-4-2 (Contact)	±8		
T _{OPT}	Operating Temperature	-55/+150	°C	
T _{STG}	Storage Temperature	-55/+150	°C	

Electrical Characteristics(Tamb=25°C)

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V _{RWM}	Reverse Working Voltage	Any I/O pin to GND			5.0	V
V _{BR}	Reverse Breakdown Voltage	I⊤ = 1mA Any I/O pin to GND	6.0			V
I _R	Reverse Leakage Current	V _{RWM} = 5V Any I/O pin to GND			1	μA
V _F	Diode Forward Voltage	I _F = 15mA		0.85	1.2	V
V _{C1}	Clamping Voltage 1	I _{PP} = 1A, t _p = 8/20µs Any I/O pin to GND			15.5	V
V _{C2}	Clamping Voltage 2	I _{PP} = 5, t _p = 8/20µs Any I/O pin to GND			25	V
C _{J1}	Junction Capacitance 1	V _R = 0V, f = 1MHz Between I/O pins		0.3	0.6	pF
C _{J2}	Junction Capacitance 2	V _R = 0V, f = 1MHz Any I/O pin to GND		0.45	0.8	pF

Note: I/O pins are pin 1,2,4,5.

Electrical Characteristics Curve





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SRC0524P

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1 3 GHz GHz

STOP 3000.000000 MHz

1:-0.086 dB 900 MHz

2: -0.0336 dB 1.8 GHz

3: -0.126 dB 2.5 GHz



Fig.4 Insertion Loss S21 - I/O to I/O

6 dB/REF0 dB

Recommended Pad outline









CH1 \$21 LOG



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	0.5	0.65	0.020	0.023	
A1		0.05		0.002	
A2	0.13 0.005		005		
b	0.15	0.25	0.006	0.010	
b1	0.35	0.45	0.014	0.018	
D	2.40	2.60	0.094	0.102	
E	0.90	1.10	0.035	0.043	
e	0.5		0.020		
L	0.30	0.43	0.012	0.017	

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